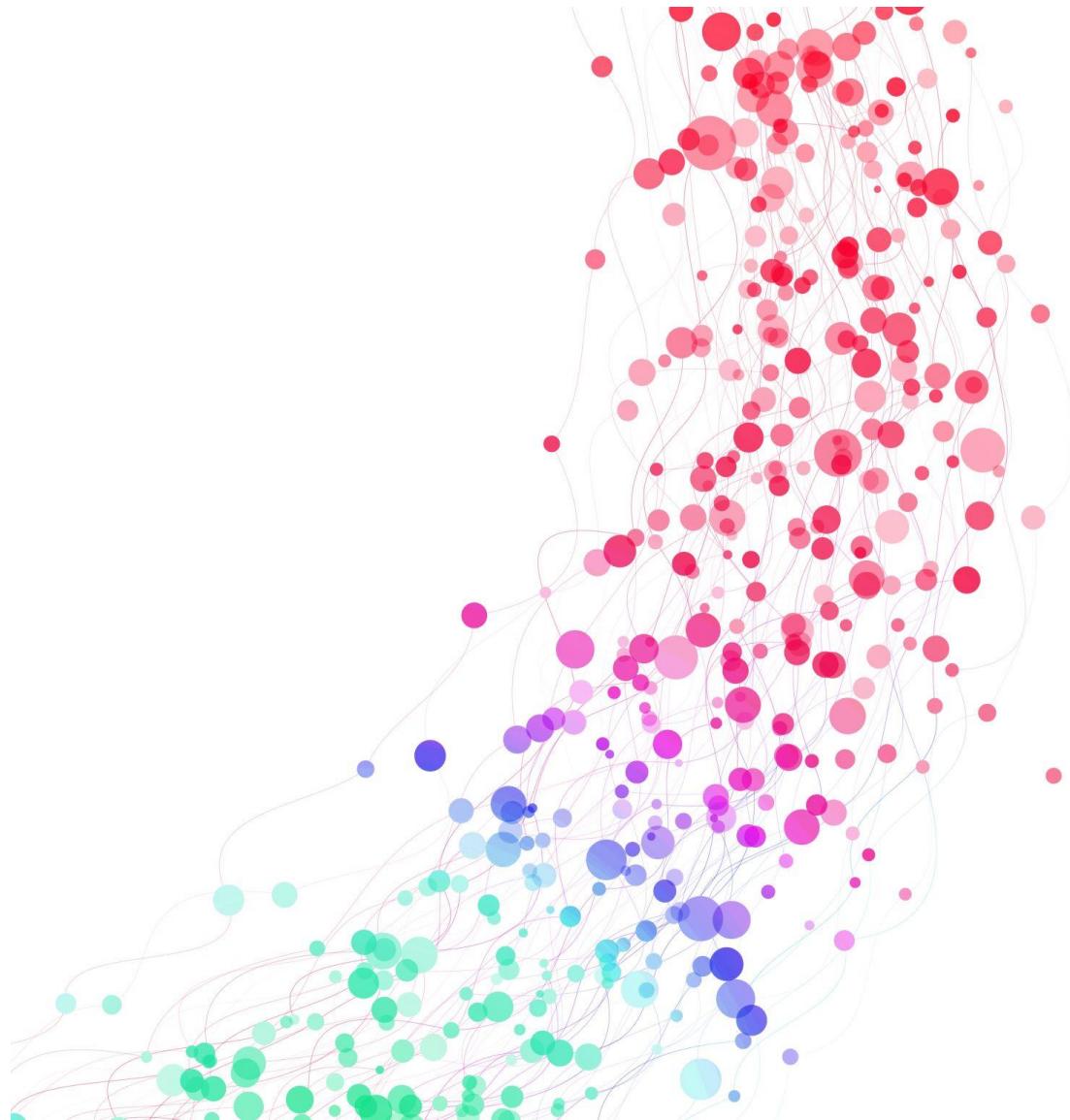
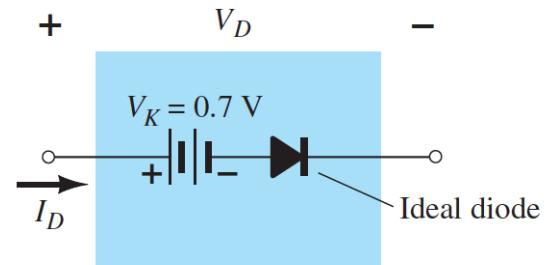
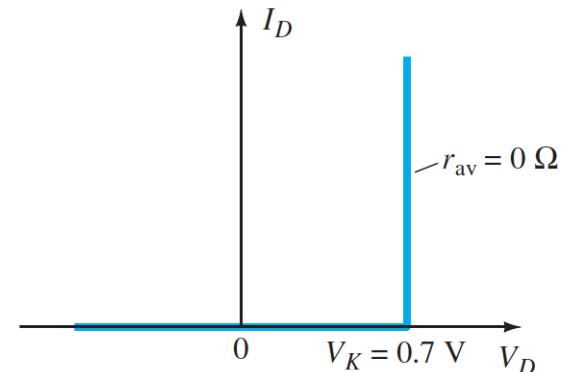
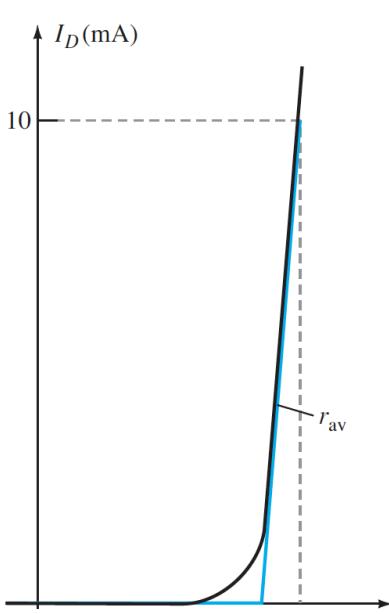
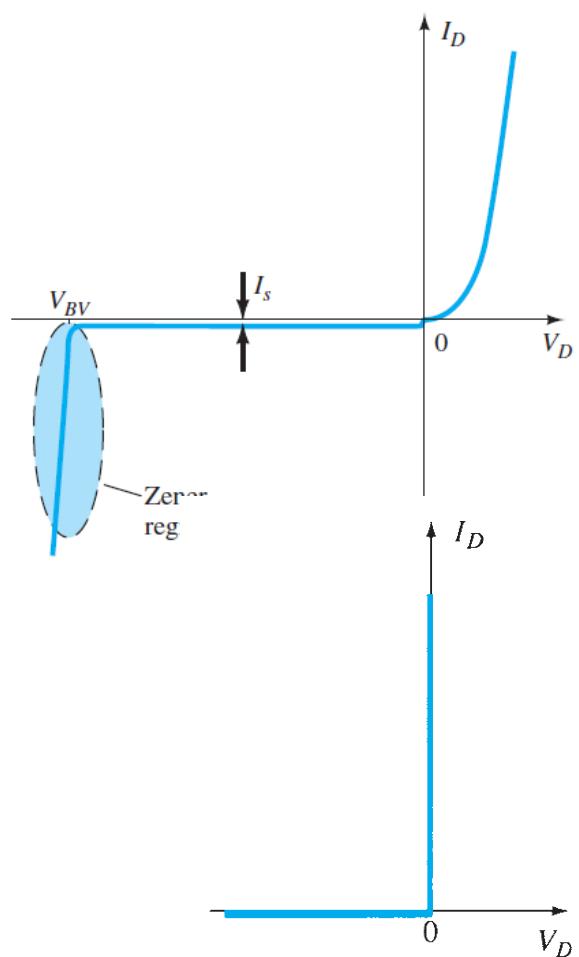


Fundamentals of Electronics

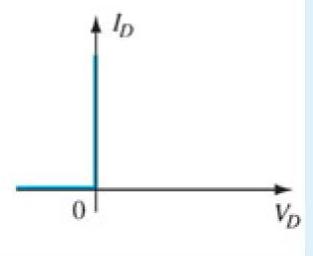
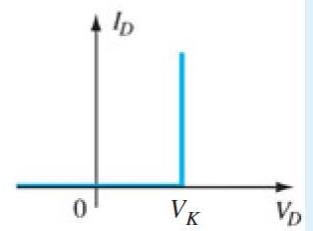
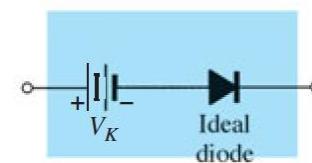
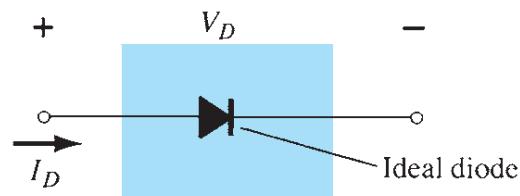
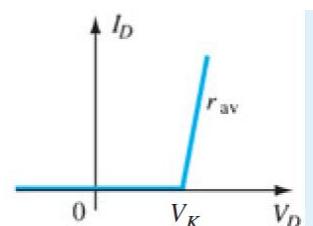
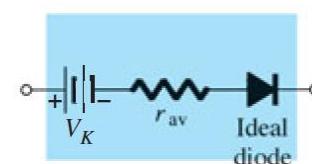
ECE 101



Summary

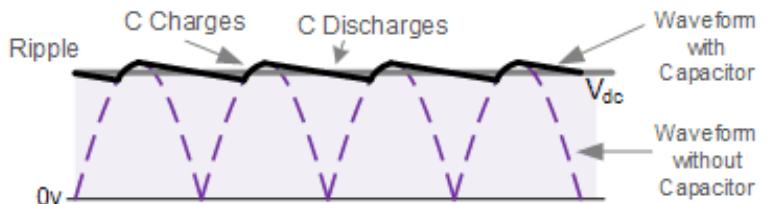
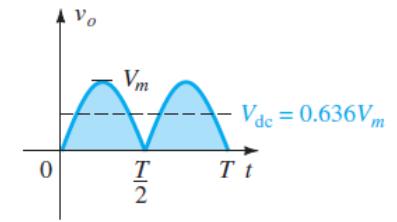
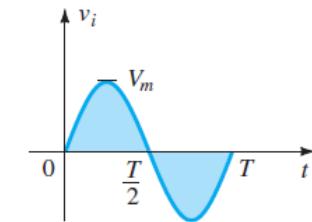
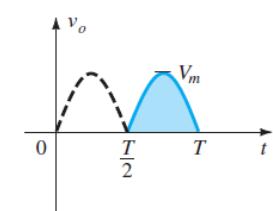
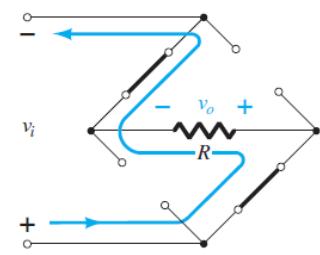
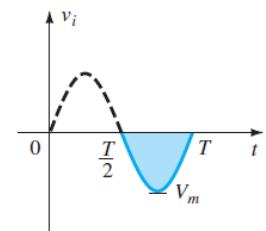
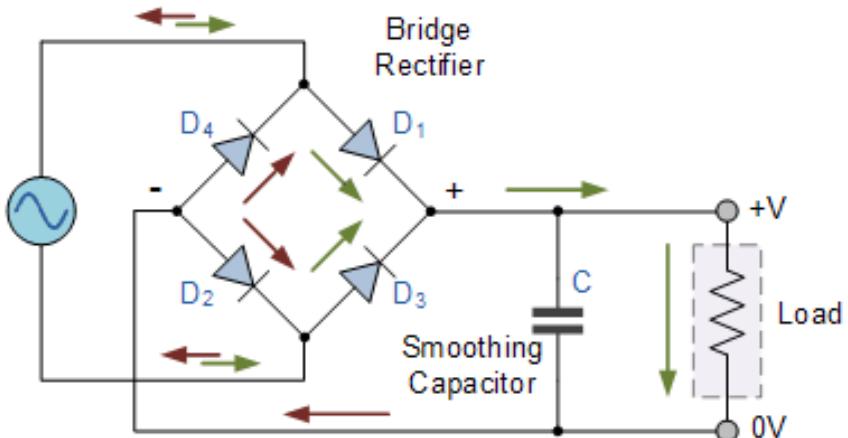
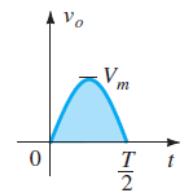
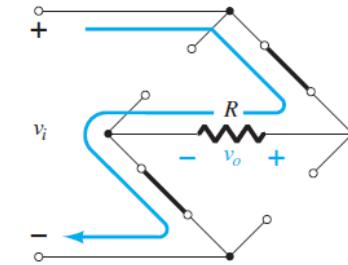
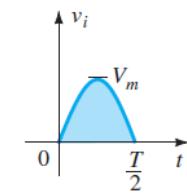
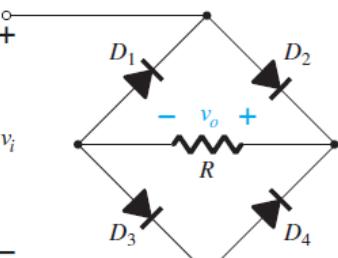
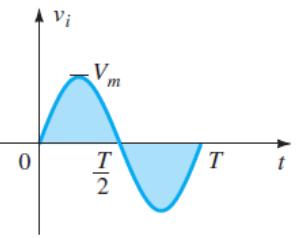


Si



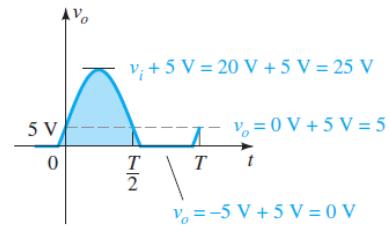
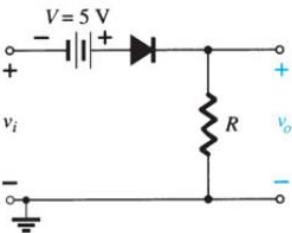
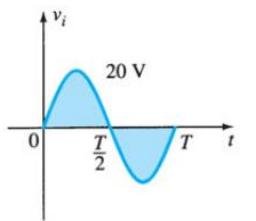
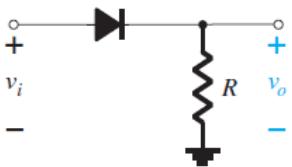
Difference b/w Semiconductors and Metals

Full wave rectification

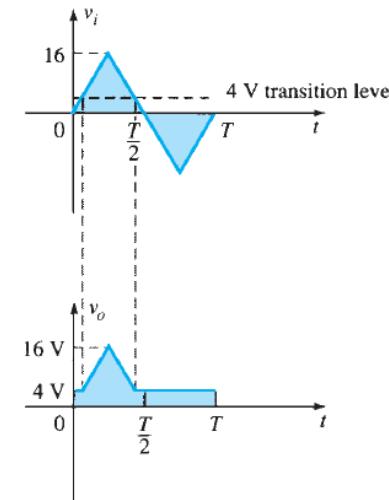
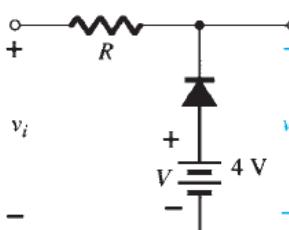
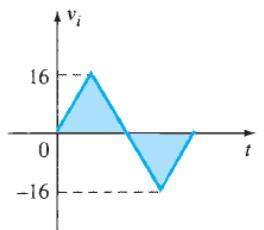
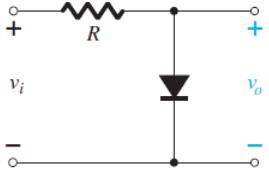


Diode as clipper

In series

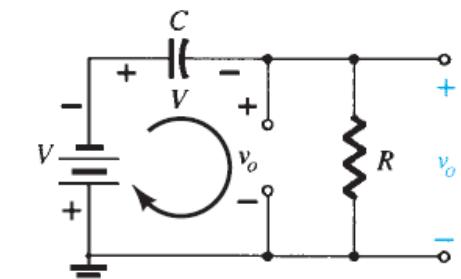
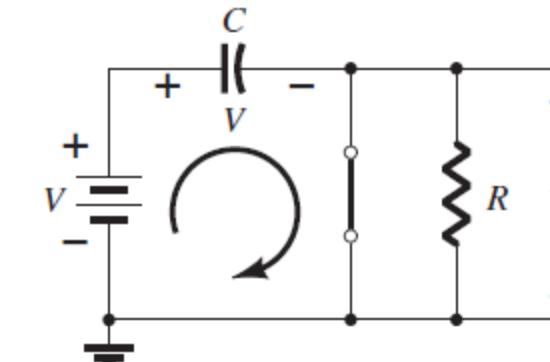
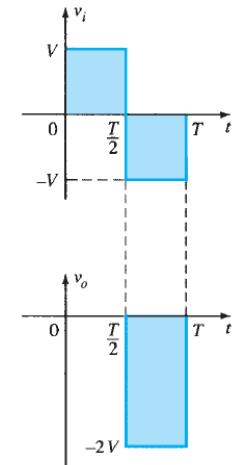
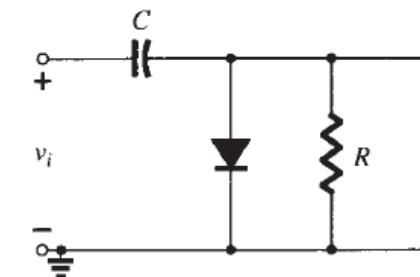
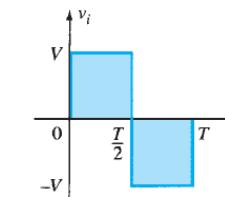


In parallel

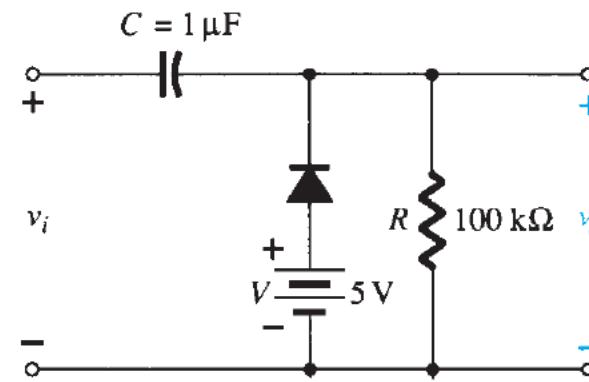
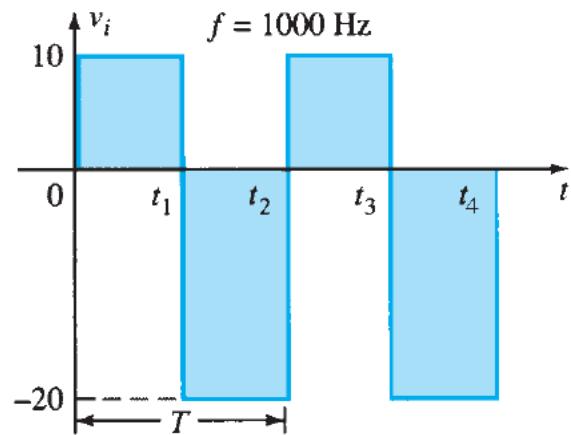


Diode as clamper

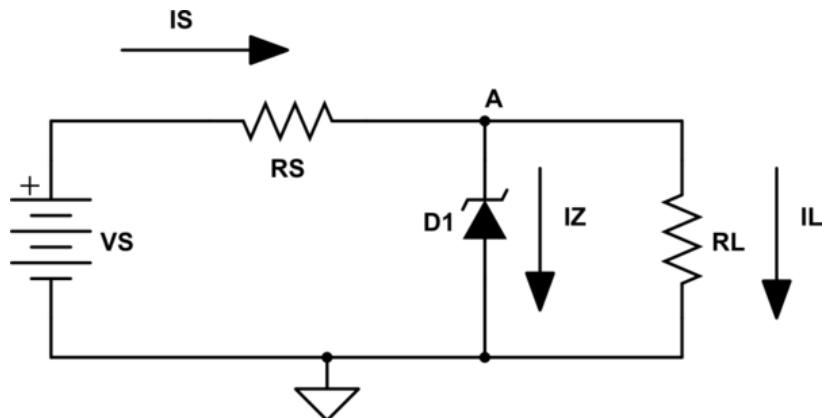
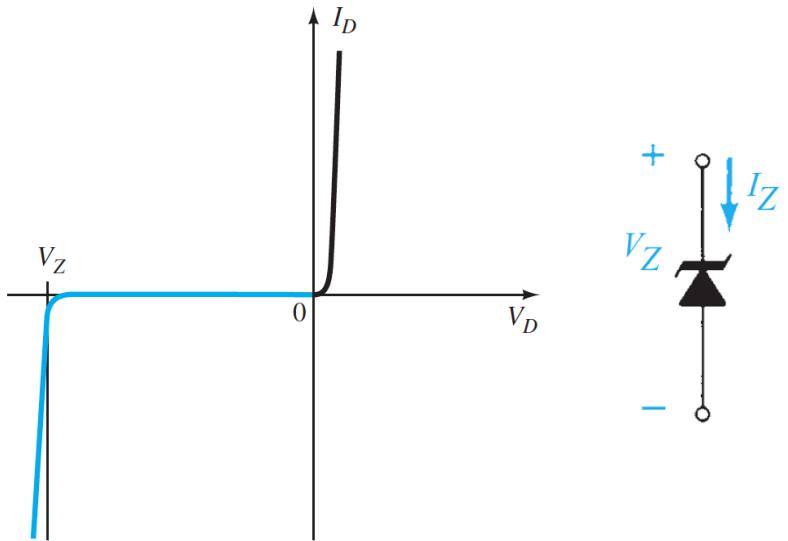
Clamper is a circuit that changes the dc level of a waveform without changing its appearance.



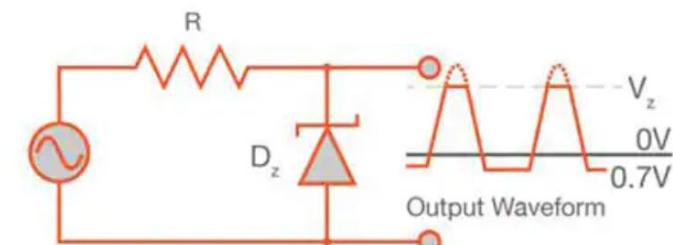
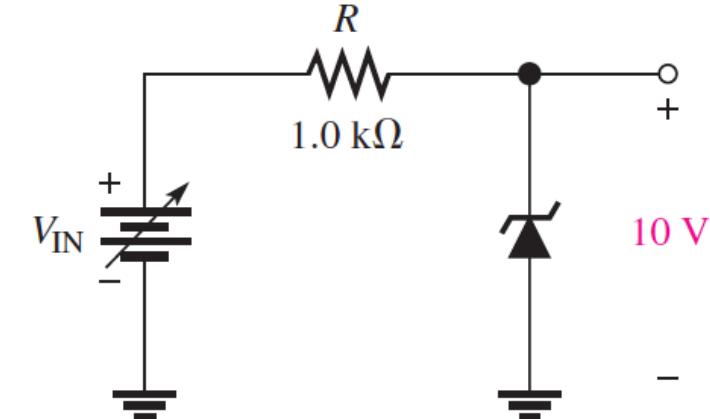
Determine the output voltage



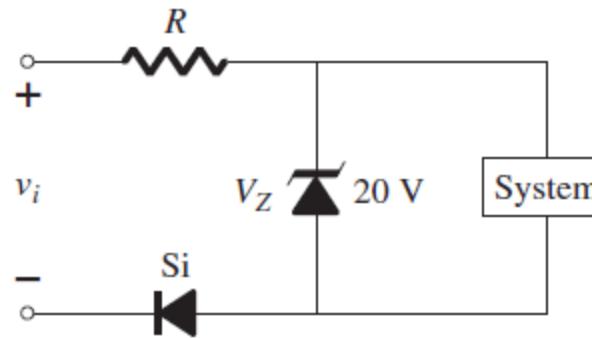
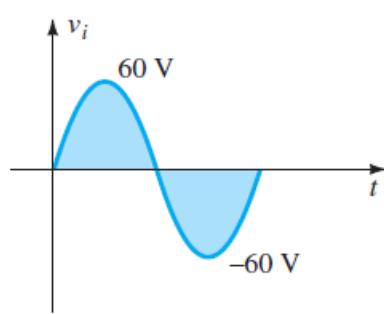
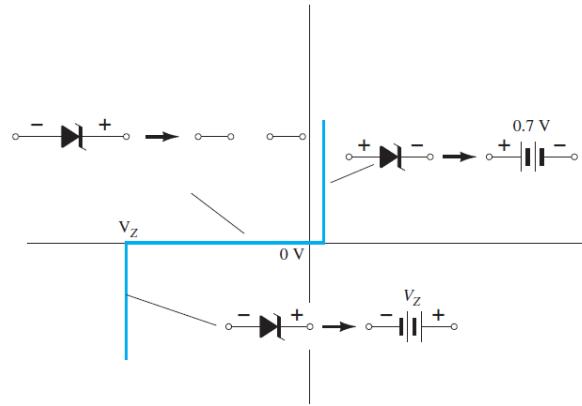
Zener Voltage Regulation



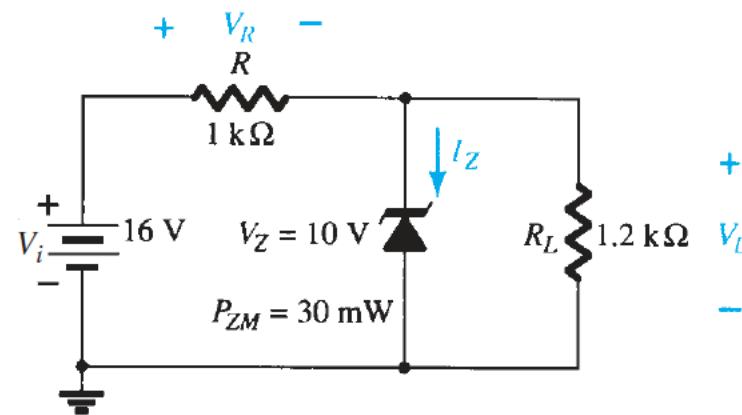
Zener regulation



Voltage regulator



- a. For the Zener diode network of Fig. 2.115, determine V_L , V_R , I_Z , and P_Z .
- b. Repeat part (a) with $R_L = 3 \text{ k}\Omega$.



The Transistor

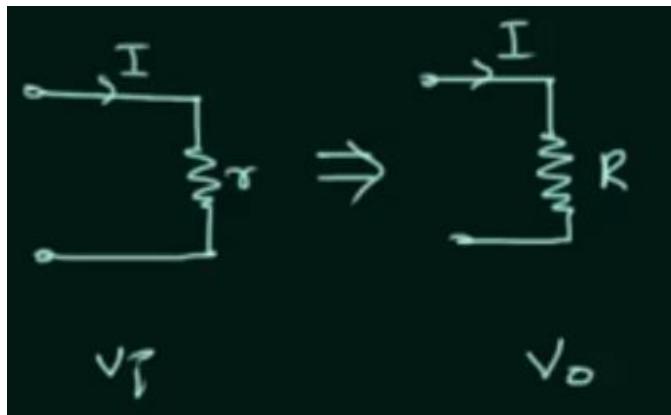
Amplification and switching

Transistor

- Key characteristic:

- The transistor is a three-terminal device with the feature that the current through two terminals can be controlled by small changes we make in the current or voltage at the third terminal.
- This control feature allows us to amplify small ac signals or to switch the device from an *on* state to an *off* state and back.
- These two operations, amplification and switching, are the basis of a host of electronic functions.
- This forms the basis for both bipolar junction transistors (BJT) and field effect transistors (FET).

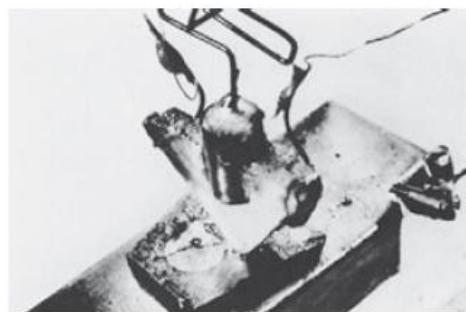
The transistor action - 1



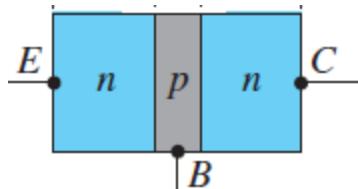
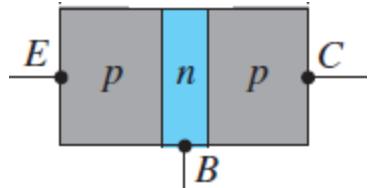
$$V_i = I \times \underline{r} \quad V_o = I \times \underline{R}$$
$$V_i < \underline{V_o} \quad (\text{amplification})$$

Active mode
 $J_1 \rightarrow f-b. \quad R_{es} = 0$
 $J_2 \rightarrow \gamma-b. \quad R_{es} = \infty$

Bipolar Junction Transistor (BJT)

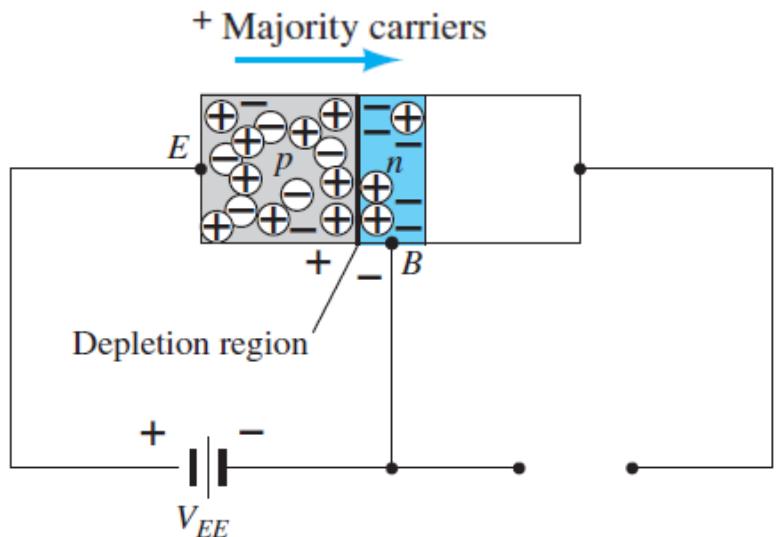


The first transistor

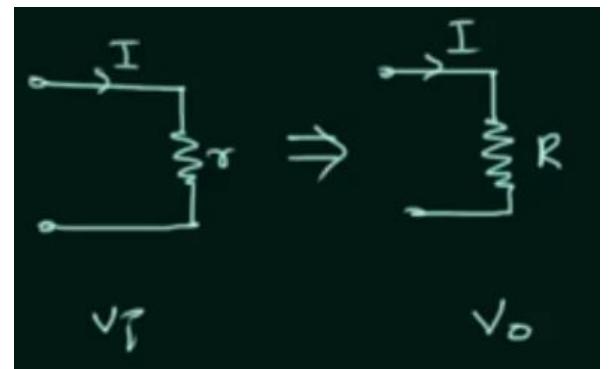
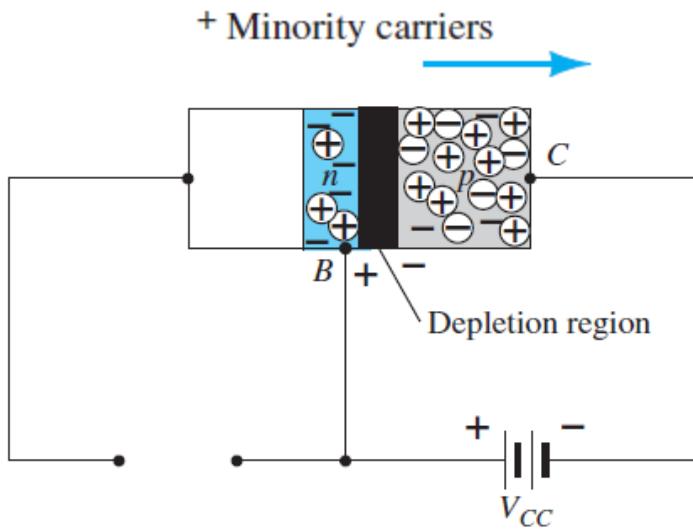


Active mode
 $J_1 \rightarrow f\text{-b. } R_{es} = 0$
 $J_2 \rightarrow r\text{-b- } R_{es} = \infty$

Basic mechanism



One p-n junction is forward biased,
the other one is reverse biased.



$$V_i = I \times \underline{r} \quad V_o = I \times \underline{R}$$
$$V_i < \underline{V_o} \quad (\text{amplification})$$

Thank you